15EC32

## Third Semester B.E. Degree Examination, Dec.2019/Jan.2020 Analog Electronics

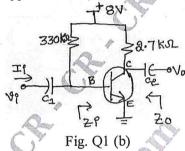
Time: 3 hrs.

Max. Marks: 80

Note: Answer FIVE full questions, choosing one full question from each module.

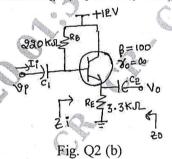
Module-1

- a. Draw the circuit diagram of common Emitter fixed bias configuration. Derive the expression for Z<sub>i</sub> Z<sub>o</sub>, A<sub>v</sub> using r<sub>e</sub> model. (08 Marks)
  - b. For the network shown in Fig. Q1 (b), determine  $Z_i$   $Z_o$ ,  $A_v$  and  $A_i$ . Given  $h_{ie} = 1.175$  K $\Omega$ ,  $h_{fe} = 120$ ,  $h_{oe} = 20$   $\mu$ A/v using approximate hybrid equivalent model. (08 Marks)



OR

- a. Draw 'r<sub>e</sub>' and 'h'-parameter models for a transistor in common Emitter configuration. Also give relation between 'r<sub>e</sub>' and 'h'-parameter. (05 Marks)
  - b. For the circuit shown below, calculate  $r_e$ ,  $Z_i$   $Z_o$  and  $A_v$ , while consider  $r_0 = \infty$ . (08 Marks)



c. What are the advantages of h-parameters?

(03 Marks)

Module-2

3 a. Explain the small signal model of the FET.

(04 Marks)

b. Derive the expression for  $Z_i$   $Z_0$  and  $A_v$  for FET voltage divider bias circuit.

(08 Marks)

c. Compare JFET and MOSFET.

(04 Marks)

OR

4 a. Explain the n-channel enhancement type MOSFETs, with their characteristics curves.

(08 Marks)

b. Derive the expression for Z<sub>i</sub> Z<sub>o</sub> and A<sub>v</sub> for FET self biased configuration (with R<sub>s</sub> bypassed).
(08 Marks)

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2. Any revealing of identification, appeal to evaluator and /or equations written eg, 42+8 = 50, will be treated as malpractice. Important Note: 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.

## Module-3

5 a. Prove that

Input capacitance is  $C_{Mi} = (1 - A_v)C_f$  and

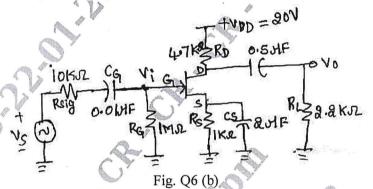
Output capacitance is  $C_{MO} = \left(1 - \frac{1}{A_{tr}}\right)C_f$  using miller effect.

(08 Marks)

b. Describe the factors that affect the low frequency response of a BJT-CE amplifier. (08 Marks)

OR

- 6 a. Explain high frequency response of FET amplifier and derive expression for cut off frequencies, defined by input and output circuits (f<sub>Hi</sub> and f<sub>Ho</sub>). (08 Marks)
  - b. Determine the lower cut off frequency for the network shown in Fig. Q6 (b), using following parameters  $g_m = 2$  ms,  $r_d = \infty \Omega$ ,  $I_{DSS} = 8$  mA,  $V_P = -4V$ ,  $V_{DD} = 20$  V. (08 Marks)



Module-4

- 7 a. With the help of a neat circuit diagram, explain the working of Hartley oscillator. (08 Marks)
  - b. The following data for Colpitts oscillator are as follows:  $C_1 = 1$  nF,  $C_2 = 99$  nF, L = 1.5 mH and  $h_{fe} = 110$ . Calculate frequency of oscillation for the same. (04 Marks)
  - c. Explain the important advantages of a negative feedback amplifier.

(04 Marks)

OR

- 8 a. Mention the types of feedback connections. Draw their block diagrams indicating input and output signal. (08 Marks)
  - b. Obtain expression for Z<sub>if</sub>, Z<sub>of</sub> for a voltage series feedback.

(08 Marks)

Module-5

- 9 a. Explain the operation of a class B push-pull amplifier and also show that its efficiency 78.50%. (08 Marks)
  - b. With a neat circuit diagram, explain the operation of a transformer coupled class A power amplifier. (08 Marks)

OR

10 a. For a harmonic distortion reading of  $D_2 = 0.1$ ,  $D_3 = 0.02$  and  $D_4 = 0.01$ , with  $I_1 = 4$  A and  $R_C = 8 \Omega$ , calculate the total harmonic distortion, fundamental power and total power.

(04 Marks)

- b. What are the classification of power amplifiers, based on the location of Q point? Discuss them briefly. (08 Marks)
- c. With the help of neat block diagram, explain the working of shunt voltage regulator.

(04 Marks)

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